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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	84MHz
Connectivity	I ² C, IrDA, LINbus, SDIO, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	50
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f401rct6

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3.14 Power supply supervisor

3.14.1 Internal reset ON

This feature is available for V_{DD} operating voltage range 1.8 V to 3.6 V.

The internal power supply supervisor is enabled by holding PDR_ON high.

The devices have an integrated power-on reset (POR) / power-down reset (PDR) circuitry coupled with a Brownout reset (BOR) circuitry. At power-on, POR is always active, and ensures proper operation starting from 1.8 V. After the 1.8 V POR threshold level is reached, the option byte loading process starts, either to confirm or modify default thresholds, or to disable BOR permanently. Three BOR thresholds are available through option bytes.

The devices remain in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for an external reset circuit.

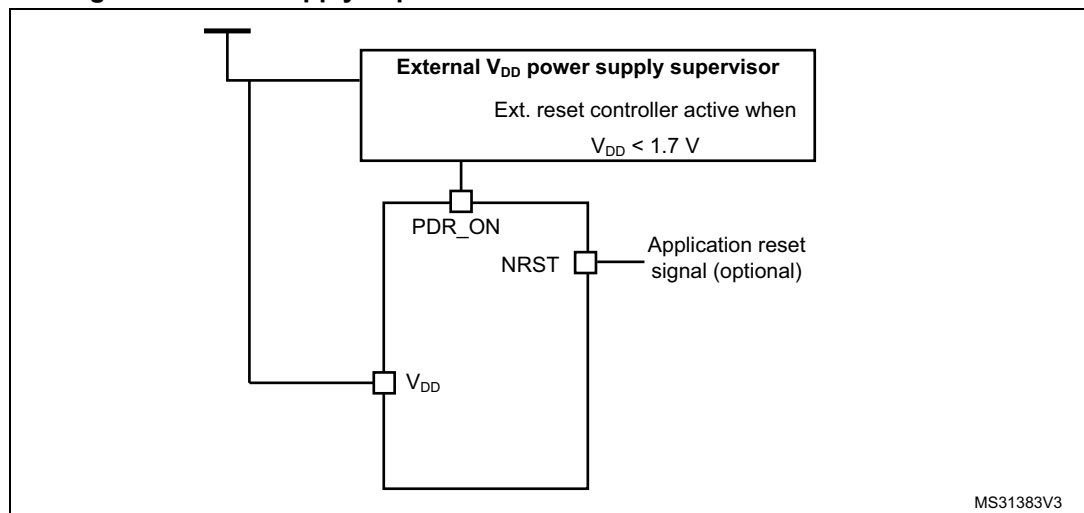
The devices also feature an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.14.2 Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled by setting the PDR_ON pin to low.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to [Figure 5: Power supply supervisor interconnection with internal reset OFF](#).

Figure 5. Power supply supervisor interconnection with internal reset OFF⁽¹⁾



1. The PRD_ON pin is only available on the WLCSP49 and UFBGA100 packages.

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4 or TIM5 timer.

3.29 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.7 V and 3.6 V. The temperature sensor is internally connected to the ADC_IN18 input channel which is used to convert the sensor output voltage into a digital value. Refer to the reference manual for additional information.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

3.30 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target.

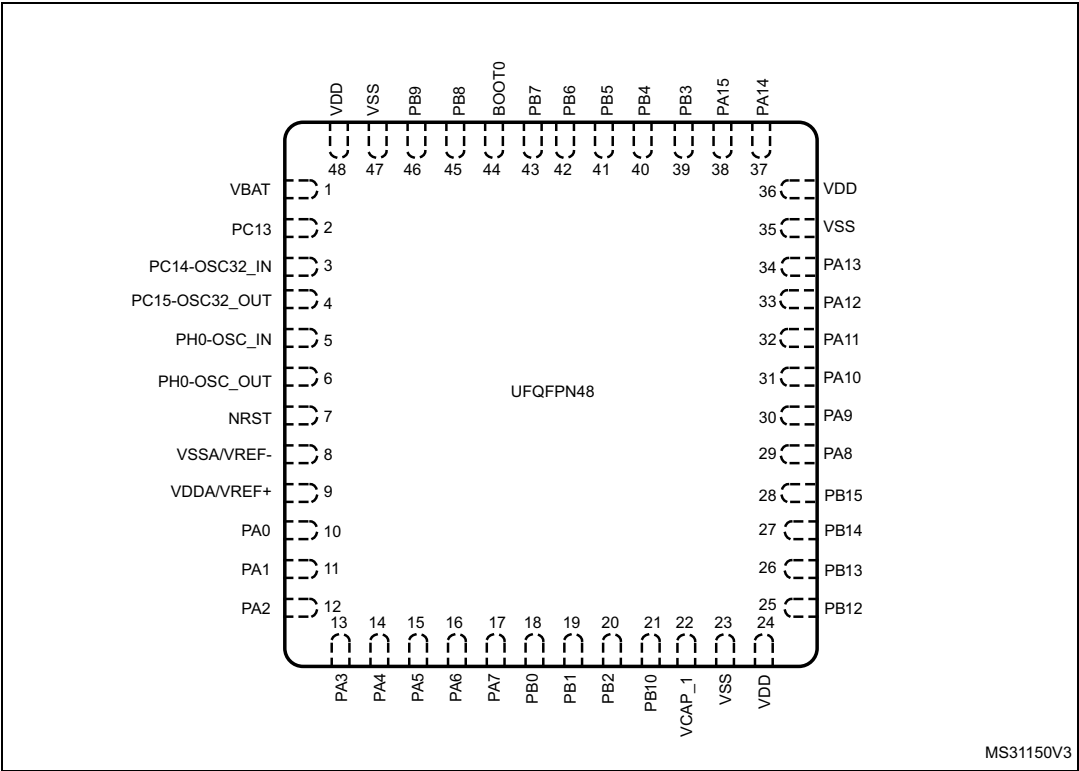
Debug is performed using 2 pins only instead of 5 required by the JTAG (JTAG pins could be re-use as GPIO with alternate function): the JTAG TMS and TCK pins are shared with SWDIO and SWCLK, respectively, and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

3.31 Embedded Trace Macrocell™

The ARM Embedded Trace Macrocell provides a greater visibility of the instruction and data flow inside the CPU core by streaming compressed data at a very high rate from the STM32F401xB/STM32F401xC through a small number of ETM pins to an external hardware trace port analyzer (TPA) device. The TPA is connected to a host computer using any high-speed channel available. Real-time instruction and data flow activity can be recorded and then formatted for display on the host computer that runs the debugger software. TPA hardware is commercially available from common development tool vendors.

The Embedded Trace Macrocell operates with third party debugger software tools.

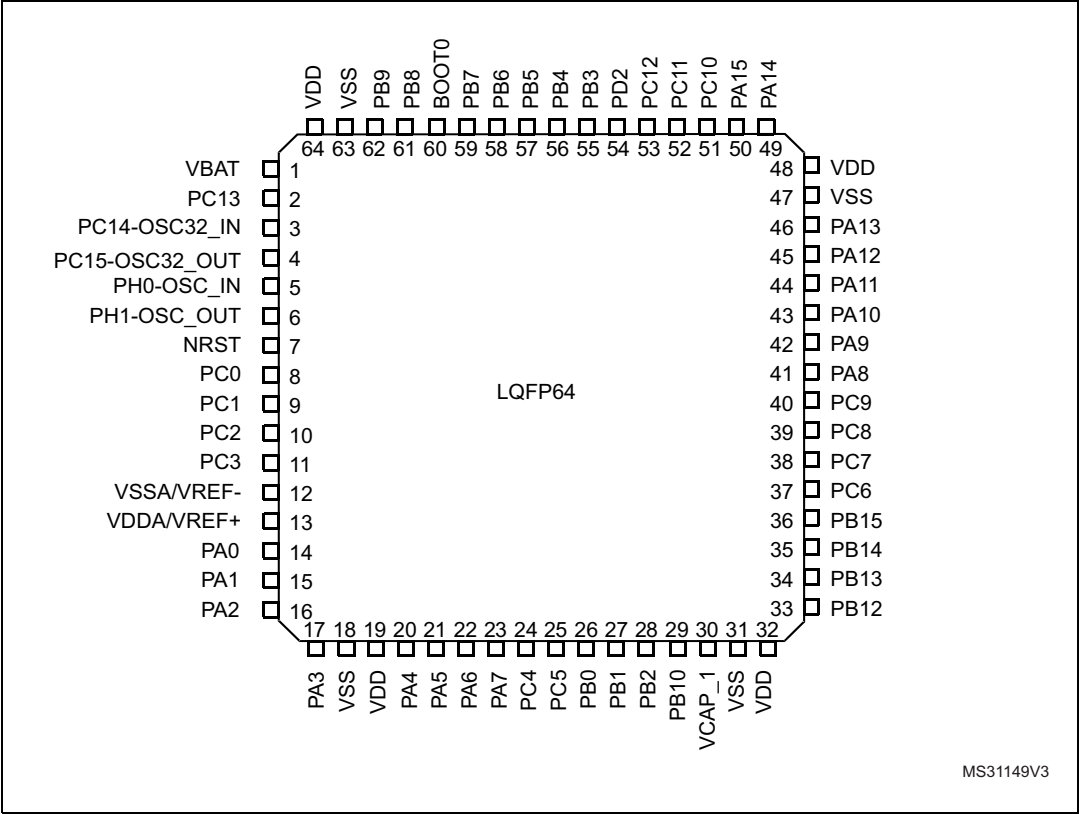
Figure 11. STM32F401xB/STM32F401xC UFQFPN48 pinout



MS31150V3

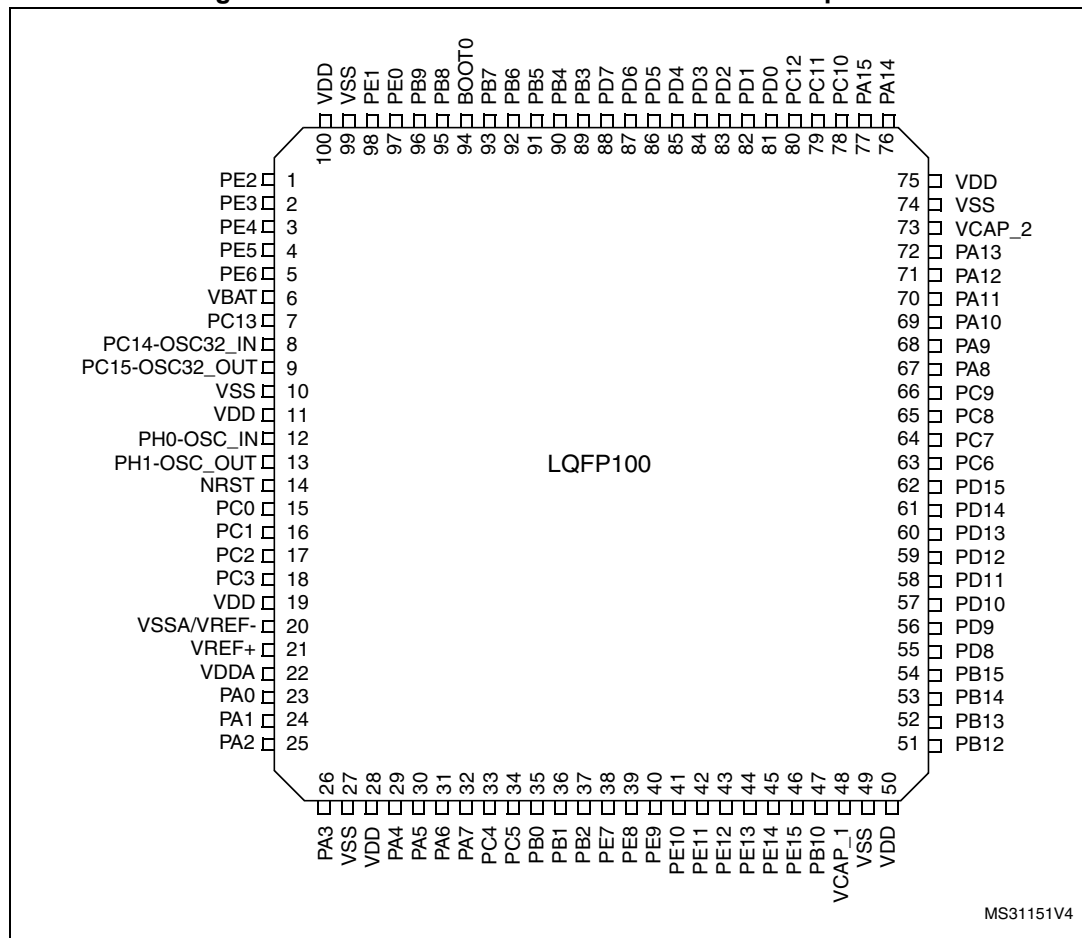
1. The above figure shows the package top view.

Figure 12. STM32F401xB/STM32F401xC LQFP64 pinout



1. The above figure shows the package top view.

Figure 13. STM32F401xB/STM32F401xC LQFP100 pinout



1. The above figure shows the package top view.

Table 8. STM32F401xB/STM32F401xC pin definitions (continued)

Pin Number					Pin name (function after reset) ⁽¹⁾	Pin type	I/O structure	Notes	Alternate functions	Additional functions
UQFN48	WLCSP49	LQFP64	LQFP100	UFBGA100						
-	-	-	45	M11	PE14	I/O	FT	-	SPI4_MOSI, TIM1_CH4, EVENTOUT	-
-	-	-	46	M12	PE15	I/O	FT	-	TIM1_BKIN, EVENTOUT	-
21	E3	29	47	L10	PB10	I/O	FT	-	SPI2_SCK/I2S2_CK, I2C2_SCL, TIM2_CH3, EVENTOUT	-
-	-	-	-	K9	PB11	I/O	FT	-	TIM2_CH4, I2C2_SDA, EVENTOUT	-
22	G2	30	48	L11	VCAP_1	S	-	-	-	-
23	D3	31	49	F12	VSS	S	-	-	-	-
24	F2	32	50	G12	VDD	S	-	-	-	-
25	E2	33	51	L12	PB12	I/O	FT	-	SPI2_NSS/I2S2_WS, I2C2_SMBA, TIM1_BKIN, EVENTOUT	-
26	G1	34	52	K12	PB13	I/O	FT	-	SPI2_SCK/I2S2_CK, TIM1_CH1N, EVENTOUT	-
27	F1	35	53	K11	PB14	I/O	FT	-	SPI2_MISO, I2S2ext_SD, TIM1_CH2N, EVENTOUT	-
28	E1	36	54	K10	PB15	I/O	FT	-	SPI2_MOSI/I2S2_SD, TIM1_CH3N, EVENTOUT	RTC_REFIN
-	-	-	55	-	PD8	I/O	FT	-	EVENTOUT	-
-	-	-	56	K8	PD9	I/O	FT	-	EVENTOUT	-
-	-	-	57	J12	PD10	I/O	FT	-	EVENTOUT	-
-	-	-	58	J11	PD11	I/O	FT	-	EVENTOUT	-
-	-	-	59	J10	PD12	I/O	FT	-	TIM4_CH1, EVENTOUT	-
-	-	-	60	H12	PD13	I/O	FT	-	TIM4_CH2, EVENTOUT	-
-	-	-	61	H11	PD14	I/O	FT	-	TIM4_CH3, EVENTOUT	-
-	-	-	62	H10	PD15	I/O	FT	-	TIM4_CH4, EVENTOUT	-
-	-	37	63	E12	PC6	I/O	FT	-	I2S2_MCK, USART6_TX, TIM3_CH1, SDIO_D6, EVENTOUT	-
-	-	38	64	E11	PC7	I/O	FT	-	I2S3_MCK, USART6_RX, TIM3_CH2, SDIO_D7, EVENTOUT	-



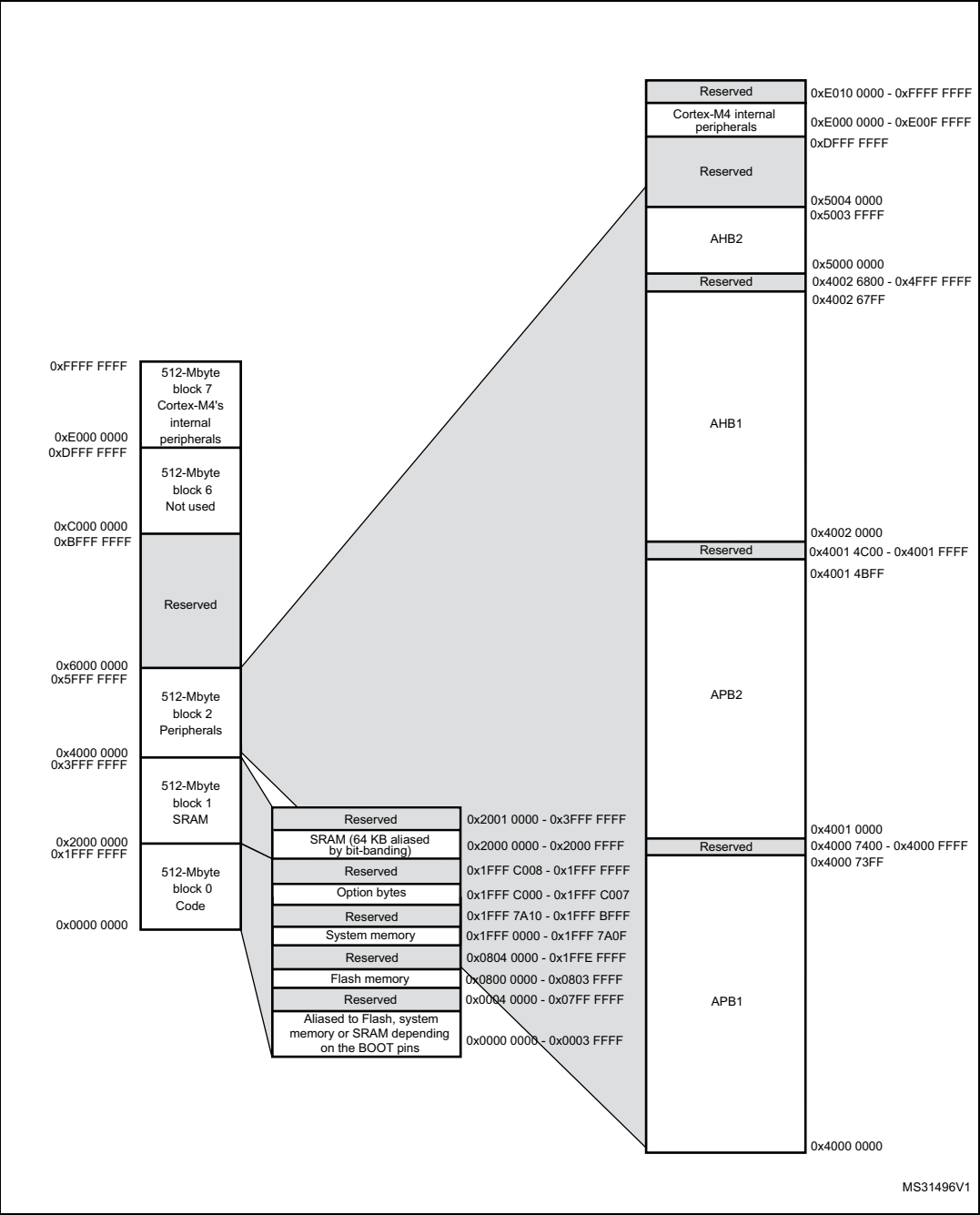
Table 9. Alternate function mapping

Port	AF00	AF01	AF02	AF03	AF04	AF05	AF06	AF07	AF08	AF09	AF10	AF11	AF12	AF13	AF14	AF15
	SYS_AF	TIM1/TIM2	TIM3/ TIM4/ TIM5	TIM9/ TIM10/ TIM11	I2C1/I2C2/ I2C3	SPI1/SPI2/ I2S2/SPI3/ I2S3/SPI4	SPI2/I2S2/ SPI3/ I2S3	SPI3/I2S3/ USART1/ USART2	USART6	I2C2/ I2C3	OTG1_FS		SDIO			
Port A	PA0	-	TIM2_CH1/ TIM2_ETR	TIM5_CH1	-	-	-	USART2_ CTS	-	-	-	-	-	-	-	EVENT OUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	USART2_ RTS	-	-	-	-	-	-	-	EVENT OUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	USART2_ TX	-	-	-	-	-	-	-	EVENT OUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	USART2_ RX	-	-	-	-	-	-	-	EVENT OUT
	PA4	-	-	-	-	SPI1_NSS	SPI3_NSS/ I2S3_WS	USART2_ CK	-	-	-	-	-	-	-	EVENT OUT
	PA5	-	TIM2_CH1/ TIM2_ETR	-	-	SPI1_SCK	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA6	-	TIM1_BKIN	TIM3_CH1	-	-	SPI1_ MISO	-	-	-	-	-	-	-	-	EVENT OUT
	PA7	-	TIM1_CH1N	TIM3_CH2	-	-	SPI1_ MOSI	-	-	-	-	-	-	-	-	EVENT OUT
	PA8	MCO_1	TIM1_CH1	-	-	I2C3_SCL	-	USART1_ CK	-	-	OTG_FS_ SOF	-	-	-	-	EVENT OUT
	PA9	-	TIM1_CH2	-	-	I2C3_ SMBA	-	USART1_ TX	-	-	OTG_FS_ VBUS	-	-	-	-	EVENT OUT
	PA10	-	TIM1_CH3	-	-	-	-	USART1_ RX	-	-	OTG_FS_I D	-	-	-	-	EVENT OUT
	PA11	-	TIM1_CH4	-	-	-	-	USART1_ CTS	USART6_ TX	-	OTG_FS_ DM	-	-	-	-	EVENT OUT
	PA12	-	TIM1_ETR	-	-	-	-	USART1_ RTS	USART6_ RX	-	OTG_FS_ DP	-	-	-	-	EVENT OUT
	PA13	JTMS SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA14	JTCK_ SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
	PA15	JTDI	TIM2_CH1/ TIM2_ETR	-	-	-	SPI1_NSS	SPI3_NSS/ I2S3_WS	-	-	-	-	-	-	-	EVENT OUT

5 Memory mapping

The memory map is shown in [Figure 15](#).

Figure 15. Memory map



6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = 3.3\text{ V}$ (for the $1.7\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

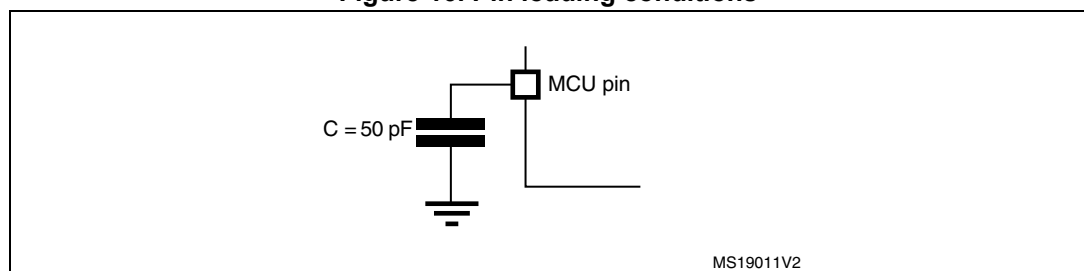
6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 16](#).

Figure 16. Pin loading conditions



6.3.4 Operating conditions at power-up / power-down (regulator OFF)

Subject to general operating conditions for T_A .

Table 18. Operating conditions at power-up / power-down (regulator OFF)⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	Power-up	20	∞	$\mu s/V$
	V_{DD} fall time rate	Power-down	20	∞	
t_{VCAP}	V_{CAP_1} and V_{CAP_2} rise time rate	Power-up	20	∞	
	V_{CAP_1} and V_{CAP_2} fall time rate	Power-down	20	∞	

1. To reset the internal logic at power-down, a reset must be applied on pin PA0 when V_{DD} reach below 1.08 V.

Note: This feature is only available for UFBGA100 package.

6.3.5 Embedded reset and power control block characteristics

The parameters given in [Table 19](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage @ 3.3V.

Table 19. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD}	Programmable voltage detector level selection	PLS[2:0]=000 (rising edge)	2.09	2.14	2.19	V
		PLS[2:0]=000 (falling edge)	1.98	2.04	2.08	
		PLS[2:0]=001 (rising edge)	2.23	2.30	2.37	
		PLS[2:0]=001 (falling edge)	2.13	2.19	2.25	
		PLS[2:0]=010 (rising edge)	2.39	2.45	2.51	
		PLS[2:0]=010 (falling edge)	2.29	2.35	2.39	
		PLS[2:0]=011 (rising edge)	2.54	2.60	2.65	
		PLS[2:0]=011 (falling edge)	2.44	2.51	2.56	
		PLS[2:0]=100 (rising edge)	2.70	2.76	2.82	
		PLS[2:0]=100 (falling edge)	2.59	2.66	2.71	
		PLS[2:0]=101 (rising edge)	2.86	2.93	2.99	
		PLS[2:0]=101 (falling edge)	2.65	2.84	2.92	
		PLS[2:0]=110 (rising edge)	2.96	3.03	3.10	
		PLS[2:0]=110 (falling edge)	2.85	2.93	2.99	
		PLS[2:0]=111 (rising edge)	3.07	3.14	3.21	
		PLS[2:0]=111 (falling edge)	2.95	3.03	3.09	
$V_{PVDhyst}^{(2)}$	PVD hysteresis		-	100	-	mV
$V_{POR/PDR}$	Power-on/power-down reset threshold	Falling edge	1.60 ⁽¹⁾	1.68	1.76	V
		Rising edge	1.64	1.72	1.80	

Table 33. Peripheral current consumption (continued)

Peripheral		I _{DD} (typ)	Unit
APB2 (up to 84MHz)	TIM1	5.71	μA/MHz
	TIM9	2.86	
	TIM10	1.79	
	TIM11	2.02	
	ADC1 ⁽²⁾	2.98	
	SPI1	1.19	
	USART1	3.10	
	USART6	2.86	
	SDIO	5.95	
	SPI4	1.31	
	SYSCFG	0.71	

1. I2SMOD bit set in SPI_I2SCFGR register, and then the I2SE bit set to enable I2S peripheral.
2. When the ADC is ON (ADON bit set in the ADC_CR2 register), add an additional power consumption of 1.6 mA for the analog part.

6.3.7 Wakeup time from low-power modes

The wakeup times given in [Table 34](#) are measured starting from the wakeup event trigger up to the first instruction executed by the CPU:

- For Stop or Sleep modes: the wakeup event is WFE.
- WKUP (PA0) pin is used to wakeup from Standby, Stop and Sleep modes.

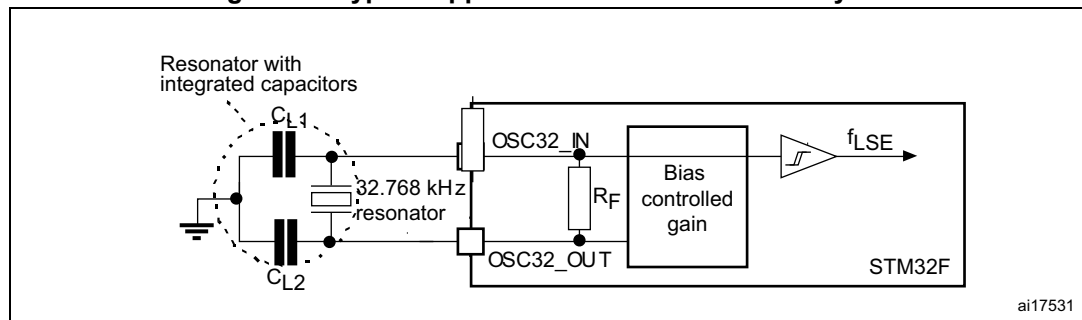
All timings are derived from tests performed under ambient temperature and V_{DD}=3.3 V.

Table 34. Low-power mode wakeup timings⁽¹⁾

Symbol	Parameter	Min ⁽¹⁾	Typ ⁽¹⁾	Max ⁽¹⁾	Unit
t _{WUSLEEP} ⁽²⁾	Wakeup from Sleep mode	-	4	6	CPU clock cycle
t _{WUSTOP} ⁽²⁾	Wakeup from Stop mode, usage of main regulator	-	13.5	14.5	μs
	Wakeup from Stop mode, usage of main regulator, Flash memory in Deep power down mode	-	105	111	
	Wakeup from Stop mode, regulator in low power mode	-	21	33	
	Wakeup from Stop mode, regulator in low power mode, Flash memory in Deep power down mode	-	113	130	
t _{WUSTDBY} ⁽²⁾⁽³⁾	Wakeup from Standby mode	-	314	407	μs

1. Guaranteed by characterization.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
3. t_{WUSTDBY} maximum value is given at -40 °C.

Figure 25. Typical application with a 32.768 kHz crystal



6.3.9 Internal clock source characteristics

The parameters given in [Table 39](#) and [Table 40](#) are derived from tests performed under ambient temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

High-speed internal (HSI) RC oscillator

Table 39. HSI oscillator characteristics ⁽¹⁾

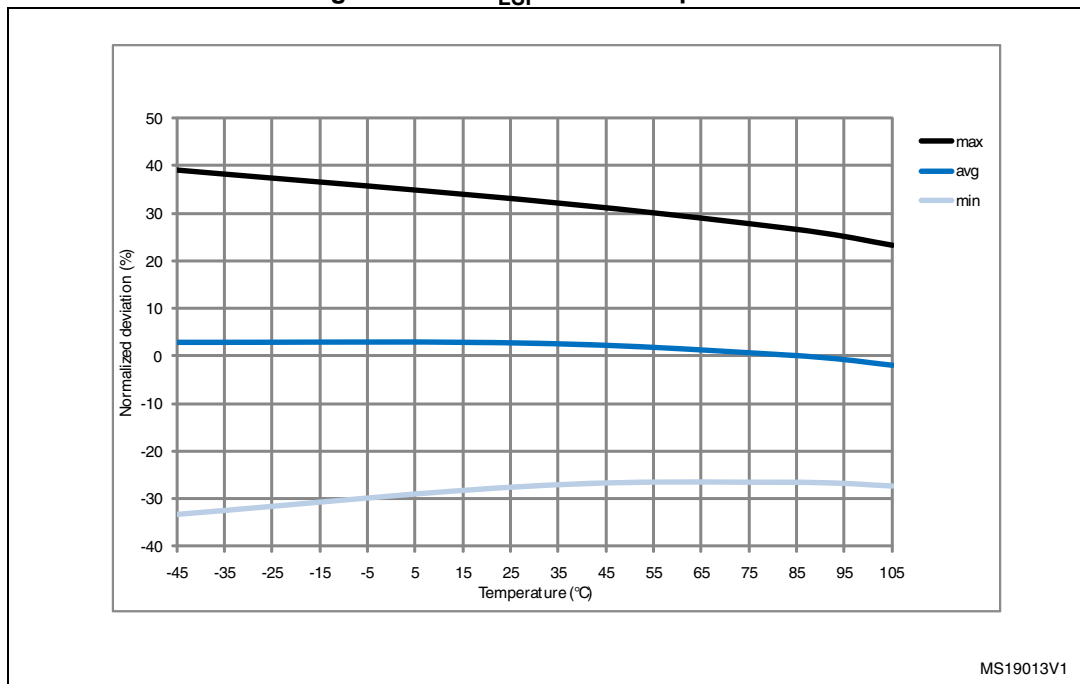
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	16	-	MHz
ACC_{HSI}	HSI user trimming step ⁽²⁾	-	-	-	1	%
	Accuracy of the HSI oscillator	$T_A = -40$ to $105\text{ }^{\circ}\text{C}$ ⁽³⁾	-8	-	4.5	%
		$T_A = -10$ to $85\text{ }^{\circ}\text{C}$ ⁽³⁾	-4	-	4	%
		$T_A = 25\text{ }^{\circ}\text{C}$ ⁽⁴⁾	-1	-	1	%
$t_{su(HSI)}$ ⁽²⁾	HSI oscillator startup time	-	-	2.2	4	μs
$I_{DD(HSI)}$ ⁽²⁾	HSI oscillator power consumption	-	-	60	80	μA

1. $V_{DD} = 3.3\text{ V}$, $T_A = -40$ to $105\text{ }^{\circ}\text{C}$ unless otherwise specified.

2. Guaranteed by design.

3. Guaranteed by characterization.

4. Factory calibrated, parts not soldered.

Figure 27. ACC_{LSI} versus temperature

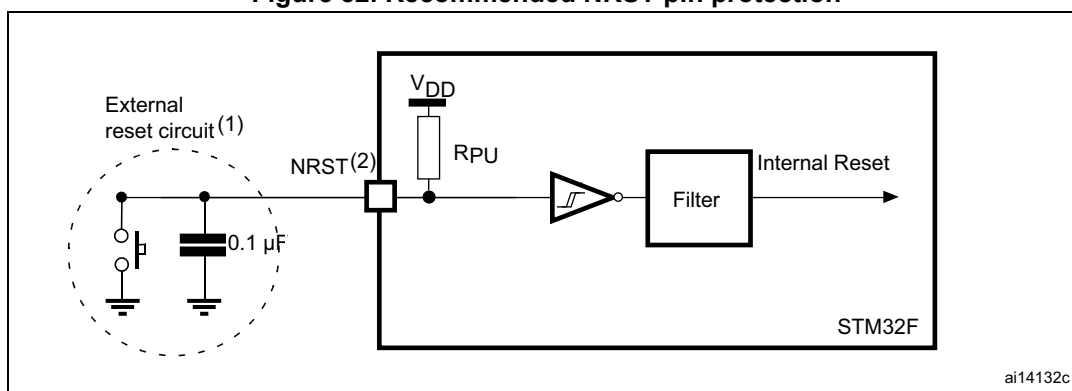
6.3.10 PLL characteristics

The parameters given in [Table 41](#) and [Table 42](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 14](#).

Table 41. Main PLL characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
f _{PLL_IN}	PLL input clock ⁽¹⁾			0.95 ⁽²⁾	1	2.10	MHz
f _{PLL_OUT}	PLL multiplier output clock			24	-	84	MHz
f _{PLL48_OUT}	48 MHz PLL multiplier output clock			-	48	75	MHz
f _{VCO_OUT}	PLL VCO output			192	-	432	MHz
t _{LOCK}	PLL lock time	VCO freq = 192 MHz		75	-	200	μs
		VCO freq = 432 MHz		100	-	300	
Jitter ⁽³⁾	Cycle-to-cycle jitter	System clock 84 MHz	RMS	-	25	-	ps
			peak to peak	-	±150	-	
	Period Jitter		RMS	-	15	-	
			peak to peak	-	±200	-	

Figure 32. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The external capacitor must be placed as close as possible to the device.
3. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in [Table 57](#). Otherwise the reset is not taken into account by the device.

6.3.18 TIM timer characteristics

The parameters given in [Table 58](#) are guaranteed by design.

Refer to [Section 6.3.16: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Table 58. TIMx characteristics⁽¹⁾⁽²⁾

Symbol	Parameter	Conditions ⁽³⁾	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APBx prescaler=1 or 2 or 4, $f_{TIMxCLK} = 84\text{ MHz}$	1	-	$t_{TIMxCLK}$
			11.9	-	ns
		AHB/APBx prescaler>4, $f_{TIMxCLK} = 84\text{ MHz}$	1	-	$t_{TIMxCLK}$
			11.9	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK} = 84\text{ MHz}$	0	$f_{TIMxCLK}/2$	MHz
			0	42	MHz
Res_{TIM}	Timer resolution		-	16/32	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected	$f_{TIMxCLK} = 84\text{ MHz}$	0.0119	780	μs
t_{MAX_COUNT}	Maximum possible count with 32-bit counter		-	65536×65536	$t_{TIMxCLK}$
		$f_{TIMxCLK} = 84\text{ MHz}$	-	51.1	S

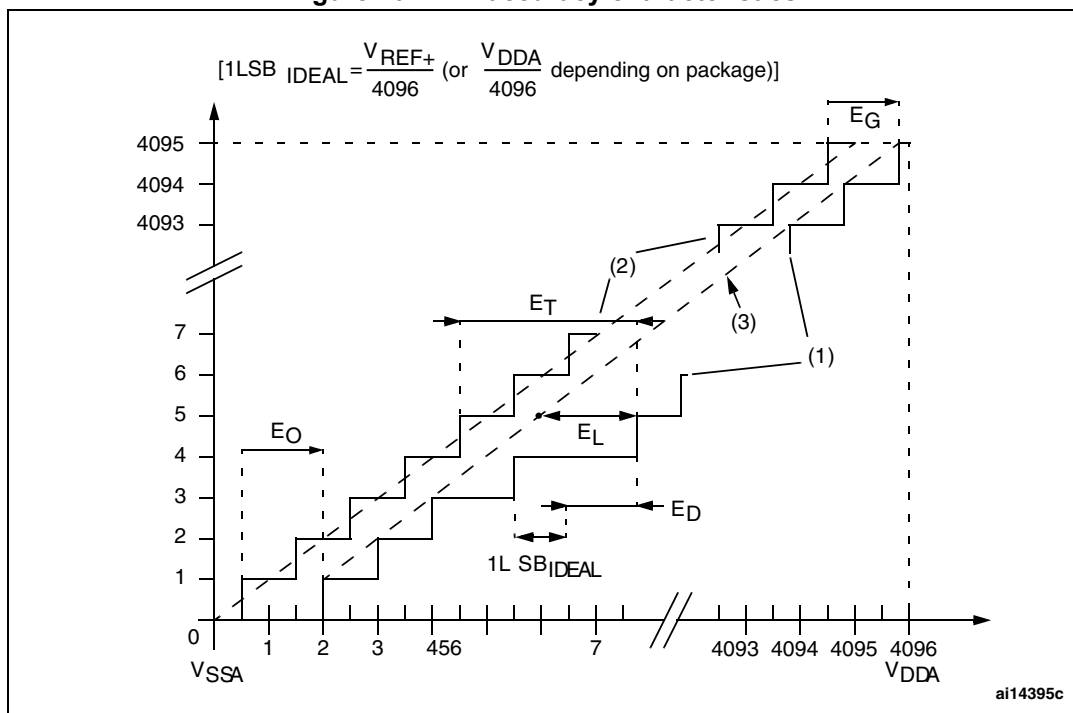
1. TIMx is used as a general term to refer to the TIM1 to TIM11 timers.
2. Guaranteed by design.
3. The maximum timer frequency on APB1 is 42 MHz and on APB2 is up to 84 MHz, by setting the TIMPRE bit in the RCC_DCKCFGR register, if APBx prescaler is 1 or 2 or 4, then $TIMxCLK = HCLK$, otherwise $TIMxCLK \geq 4 \times PCLKx$.

Table 66. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{lat}^{(2)}$	Injection trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.100	μs
			-	-	3 ⁽⁵⁾	$1/f_{ADC}$
$t_{latr}^{(2)}$	Regular trigger conversion latency	$f_{ADC} = 30\text{ MHz}$	-	-	0.067	μs
			-	-	2 ⁽⁵⁾	$1/f_{ADC}$
$t_S^{(2)}$	Sampling time	$f_{ADC} = 30\text{ MHz}$	0.100	-	16	μs
			3	-	480	$1/f_{ADC}$
$t_{STAB}^{(2)}$	Power-up time		-	2	3	μs
$t_{CONV}^{(2)}$	Total conversion time (including sampling time)	$f_{ADC} = 30\text{ MHz}$ 12-bit resolution	0.50	-	16.40	μs
		$f_{ADC} = 30\text{ MHz}$ 10-bit resolution	0.43	-	16.34	μs
		$f_{ADC} = 30\text{ MHz}$ 8-bit resolution	0.37	-	16.27	μs
		$f_{ADC} = 30\text{ MHz}$ 6-bit resolution	0.30	-	16.20	μs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$
$f_S^{(2)}$	Sampling rate ($f_{ADC} = 30\text{ MHz}$, and $t_S = 3\text{ ADC cycles}$)	12-bit resolution Single ADC	-	-	2	Msp/s
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msp/s
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msp/s
$I_{VREF+}^{(2)}$	ADC V_{REF} DC current consumption in conversion mode		-	300	500	μA
$I_{VDDA}^{(2)}$	ADC V_{DDA} DC current consumption in conversion mode		-	1.6	1.8	mA

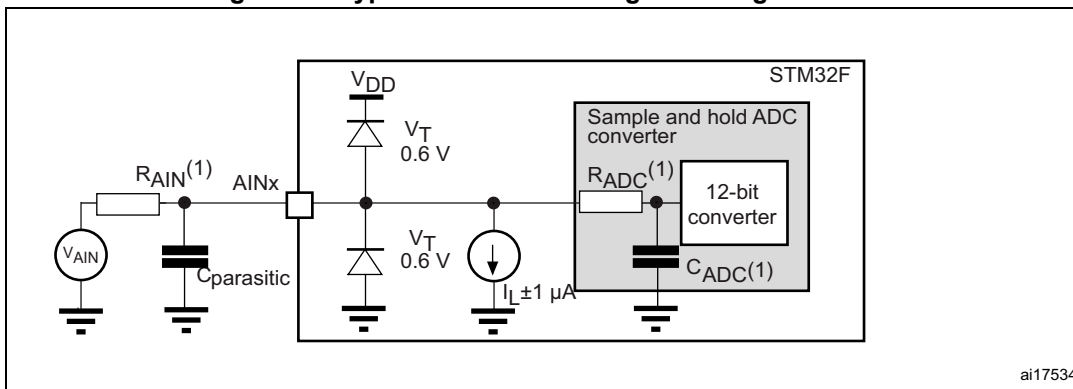
1. V_{DDA} minimum value of 1.7 V is possible with the use of an external power supply supervisor (refer to [Section 3.14.2: Internal reset OFF](#)).
2. Guaranteed by characterization.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA} .
4. R_{ADC} maximum value is given for $V_{DD}=1.7\text{ V}$, and minimum value for $V_{DD}=3.3\text{ V}$.
5. For external triggers, a delay of $1/f_{CLK2}$ must be added to the latency specified in [Table 66](#).

Figure 40. ADC accuracy characteristics



1. See also [Table 68](#).
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
 E_O = Offset Error: deviation between the first actual transition and the first ideal one.
 E_G = Gain Error: deviation between the last ideal transition and the last actual one.
 E_D = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
 E_L = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 41. Typical connection diagram using the ADC



1. Refer to [Table 66](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

Table 77. Dynamic characteristics: SD / MMC characteristics⁽¹⁾⁽²⁾ (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
CMD, D inputs (referenced to CK) in SD default mode						
t _{ISUD}	Input setup time SD	fpp = 24MHz	1.5	-	-	ns
t _{IHD}	Input hold time SD	fpp = 24MHz	0.5	-	-	
CMD, D outputs (referenced to CK) in SD default mode						
t _{OVD}	Output valid default time SD	fpp =24MHz	-	4.5	6.5	ns
t _{OHD}	Output hold default time SD	fpp =24MHz	3.5	-	-	

1. Guaranteed by characterization results.

2. $V_{DD} = 2.7$ to 3.6 V.

6.3.25 RTC characteristics

Table 78. RTC characteristics

Symbol	Parameter	Conditions	Min	Max
-	$f_{PCLK1}/RTCCLK$ frequency ratio	Any read/write operation from/to an RTC register	4	-